

Silicon Carbide (SiC) JFET - EliteSiC, Power N-Channel, TOLL, 750 V, 4.3 mohm

Rev. C, January 2025

Description

Qorvo's UJ4N075004L8S is a 750 V, $4.3m\Omega$ high-performance Gen 4 normally-on SiC JFET transistor. This device exhibits ultra-low on resistance ($R_{DS(on)}$) in a compact TOLL package, making it an ideal fit to address the challenging thermal and space constraints of solid-state circuit breakers and relay applications. Additionally, the JFET is a robust device technology capable of the high-energy switching required in circuit protection applications.

Features

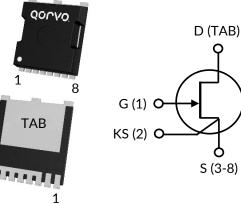
- Single digit on-resistance in a TOLL SMD package
- Operating temperature: 175°C (max)
- High pulse current capability
- Excellent device robustness
- Silver-sintered die attach for excellent thermal resistance
- Short circuit rated
- RoHS compliant
- AECQ Qualified

Typical applications

- Solid State / Semiconductor Circuit Breaker
- Solid State / Semiconductor Relay
- Battery Disconnects
- Surge Protection
- Inrush Current Control



DATASHEET



Part Number	Package	Marking
UJ4N075004L8S	MO-229	UJ4N075004



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Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
Drain-source voltage	V _{DS}		750	V
Gate-source voltage	V _{GS}	DC	-30 to +3	V
Gate-source voltage	V GS	AC ¹	-30 to +30	V
Continuous drain current ²	I _D	T _C < 145°C	120	А
Pulsed drain current ³	I _{DM}	T _c = 25°C	588	А
Short circuit withstand time	t _{sc}	V _{DS} = 400V, T _{J(START)} = 175°C	5	μs
Power dissipation	P _{tot}	T _C = 25°C	1153	W
Maximum junction temperature	T _{J,max}		175	°C
Operating and storage temperature	Tj,T _{STG}		-55 to 175	°C
Reflow soldering temperature	T _{solder}	reflow MSL 1	260	°C

1. +30V AC rating applies for turn-on pulses <200ns applied with external R_G > 1 Ω .

- 2. Limited by bondwires
- 3. Pulse width $t_{\rm p}$ limited by $T_{\rm J,max}$

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value			Units
			Min	Тур	Max	Offics
Thermal resistance, junction-to-case	$R_{ heta JC}$			0.10	0.13	°C/W

Q0000



Electrical Characteristics (T_J = +25°C unless otherwise specified)

Typical Performance - Static

Denometra	Complete	Test Conditions	iene		Value	
Parameter	Symbol	lest Conditions	Min	Тур	Max	- Units
Drain-source breakdown voltage	BV _{DS}	V _{GS} =-20V, I _D =2mA	750			V
		V _{DS} =750V,		13	120	- μΑ
Total durin lockage surrent		V _{GS} =-20V, T _J =25°C				
Total drain leakage current	I _{DSS}	V _{DS} =750V,		15		
		V _{GS} =-20V, T _J =175°C		65		
Tatal acta lackage surrent	I _{GSS}	V _{GS} =-20V, T _J =25°C		0.1	100	μA
Total gate leakage current		V _{GS} =-20V, T _J =175°C		0.3		μA
		V _{GS} =2V, I _D =80A,		4.3		
		TJ=25°C				
		V _{GS} =0V, I _D =80A,	1.0	4.0	6.6	mΩ
Drain-source on-resistance	R _{DS(on)}	TJ=25°C		4.9		
	- 505(01)	V_{GS} =2V, I_{D} =80A,		9.9		
		т _ј =175°С		7.7		
		V_{GS} =0V, I_{D} =80A,		11.5		
		т _ј =175°С		11.5		
Gate threshold voltage	V _{G(th)}	V_{DS} =5V, I_{D} =180mA	-8.3	-6.0	-3.7	V
Gate resistance	R _G	f=1MHz, open drain		0.8		Ω

Typical Performance - Dynamic

Parameter	Symbol	Test Conditions	Value			1.1	
Parameter	Symbol		Min	Тур	Max	- Units	
Input capacitance	C _{iss}	V _{DS} =400V, V _{GS} =-20V		3028			
Output capacitance	C _{oss}	f=100kHz		364		pF	
Reverse transfer capacitance	C _{rss}			360			
Effective output capacitance, energy	C	V _{DS} =0V to 400V,		440			
related	C _{oss(er)}	C _{oss(er)}	V _{GS} =-20V		448		pF
C _{OSS} stored energy	E _{oss}	V _{DS} =400V, V _{GS} =-20V		36		μJ	
Total gate charge	Q _G	V -400V I -90A		400			
Gate-drain charge	Q_{GD}	V_{DS} =400V, I_{D} =80A, V_{GS} = -18V to 0V		270		nC	
Gate-source charge	Q _{GS}	$v_{GS} = -18V$ to $0V$		60			



Typical Performance Diagrams

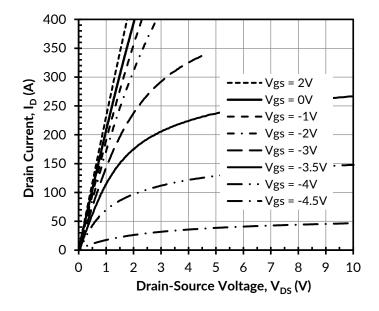
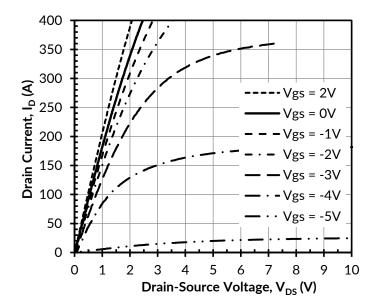


Figure 1. Typical output characteristics at $T_J = -55^{\circ}C$, tp < 250 μ s



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Figure 2. Typical output characteristics at T $_{\rm J}$ = 25°C, tp < 250 μs

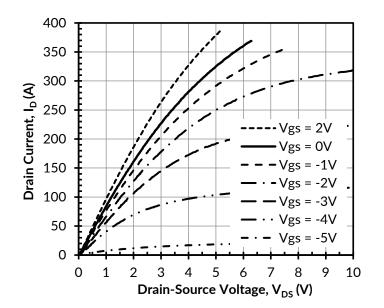


Figure 3. Typical output characteristics at $T_J = 175^{\circ}C$, tp < 250 μ s

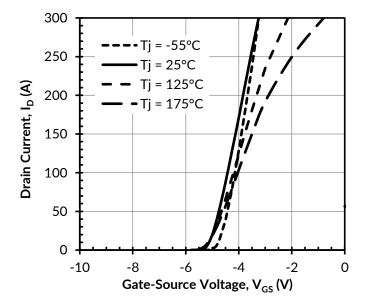


Figure 4. Typical transfer characteristics at V_{DS} = 5V

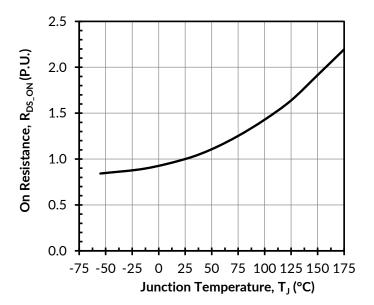
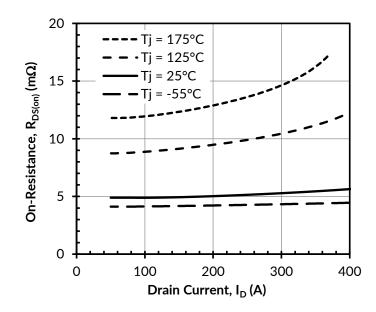


Figure 5. Normalized on-resistance vs. temperature at V_{GS} = 0V and I_D = 80A



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Figure 6. Typical drain-source on-resistances at $V_{GS} = OV$

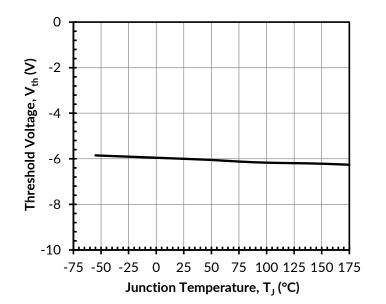


Figure 7. Threshold voltage vs. junction temperature at V_{DS} = 5V and I_D = 180mA

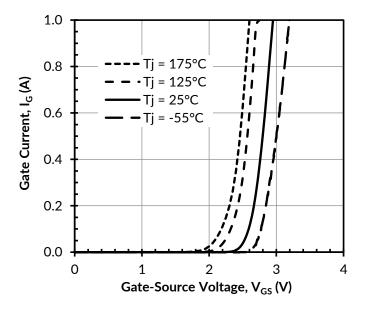
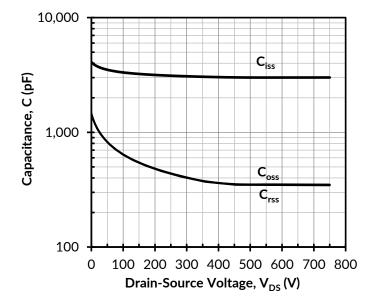
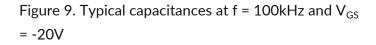


Figure 8. Typical gate forward current at V_{DS} = 0V







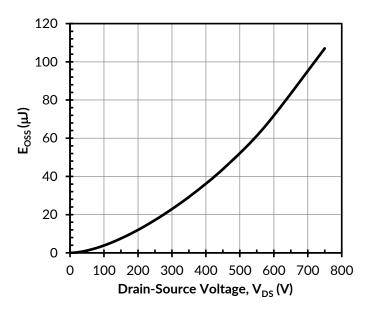


Figure 10. Typical stored energy in C_{OSS} at V_{GS} = -20V

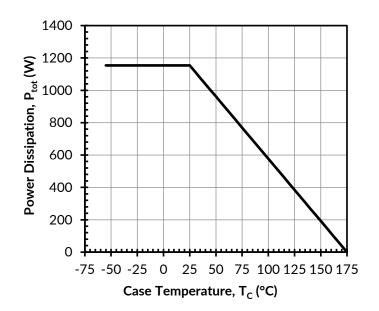
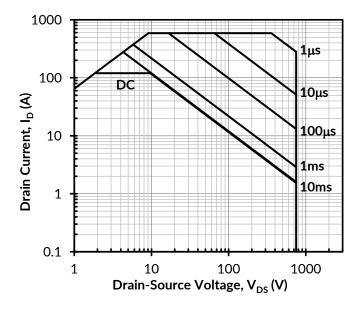


Figure 11. Total power Dissipation

Figure 12. DC drain current derating

140





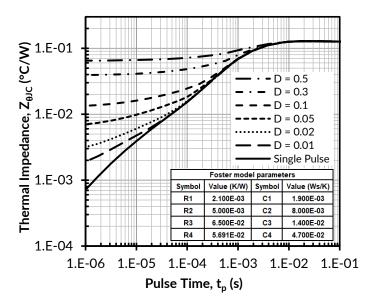


Figure 13. Safe operation area at $T_C = 25^{\circ}C$, Parameter t_p

Figure 14. Maximum transient thermal impedance

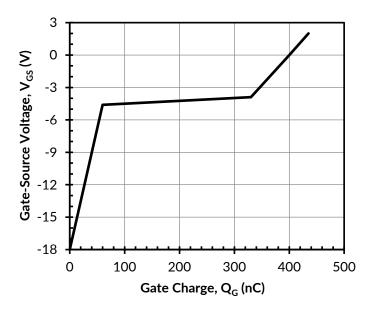
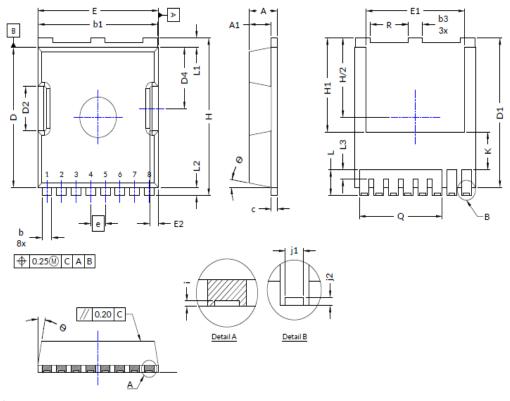


Figure 15. Typical gate charge at V_{DS} = 400V and I_{D} = 80A





Package Outlines



TO-LL					
SYMBOL	Value				
SYMBOL	Min	Nom	Max		
Α	2.15	2.30	2.45		
A1		1.80 REF			
b	0.70	0.80	0.90		
b1	9.65	9.80	9.95		
b3	1.10	1.20	1.30		
c	0.40	0.50	0.60		
D	10.18	10.38	10.58		
D1	10.98	11.08	11.18		
D2	3.15	3.15 3.30 3.45			
D4	4.40	4.40 4.55 4.70			
E	9.70	10.10			
E1	7.95	8.10	8.25		
E2	0.60	0.60 0.70			
e		1.20 BSC			
н	11.48	11.68	11.88		
H1	6.80	6.95	7.10		
i		0.10 REF			
j1		0.46 REF			
j2		0.20 REF			
К		2.80 REF			
L	1.40	1.90	2.10		
L1	0.50	0.70	0.90		
L2	0.48	0.60	0.72		
L3	0.30	0.70	0.80		
Q	6.80 REF				
R	3.00	3.10	3.20		
θ	10°				

Note:

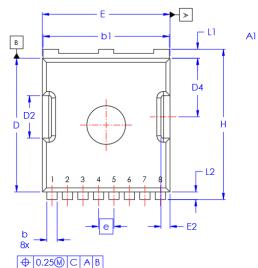
- 1. All dimensions in millimeters
- 2. Dimensions does not include Burrs and Mold Flashes
- 3. Dimensions in compliance with JEDEC MO-299B except for backside
- heatsink exposed pad dimension, E1 and H1
- Pin Designations: 1 : Gate
- 2 : Source Kelvin
- 3-8 : Source

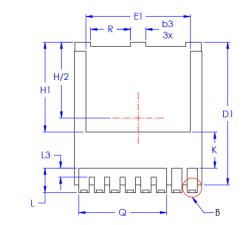
Important notice

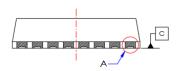
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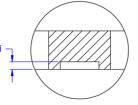


PACKAGE OUTLINE

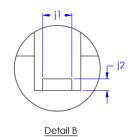








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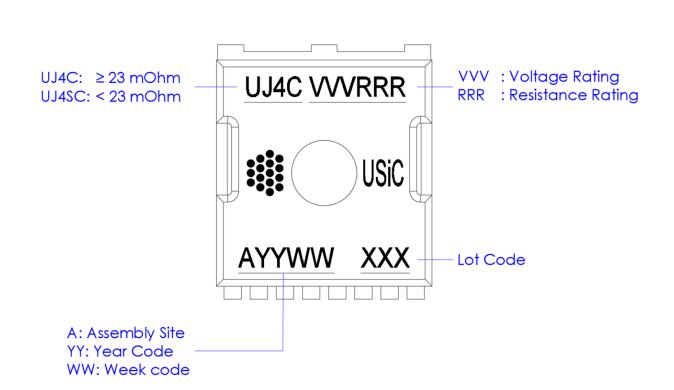
<u>Detail A</u>

- Note: 1. All dimensions in millimeters
 - 2. Dimensions does not include Burrs and Mold Flashes

	TO-LL			
SYMBOL	Value			
	Min	Max		
A	2.15	2.45		
Al	1.80	REF		
b	0.65	0.90		
bl	9.65	9.95		
b3	1.10	1.30		
С	0.40	0.60		
D	10.18	10.58		
D1	10.88	11.28		
D2	3.15	3.45		
D4	4.40	4.70		
E	9.70	10.10		
E1	7.95	8.25		
E2	0.60	0.80		
е	1.20	BSC		
Н	11.48	11.88		
H1	6.80	7.10		
i	0.10	REF		
jl	0.46	REF		
j2	0.20	REF		
K	2.80	REF		
L	1.40	2.10		
LI	0.50	0.90		
L2	0.48	0.72		
L3	0.30	0.80		
Q	6.80 REF			
R	3.00	3.20		



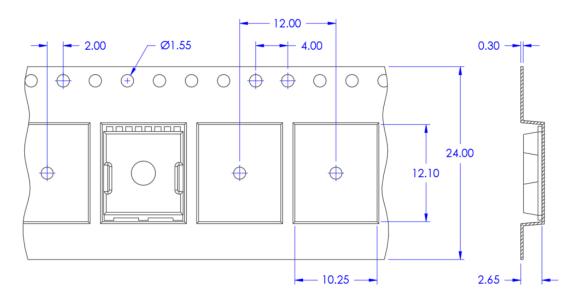
PART MARKING



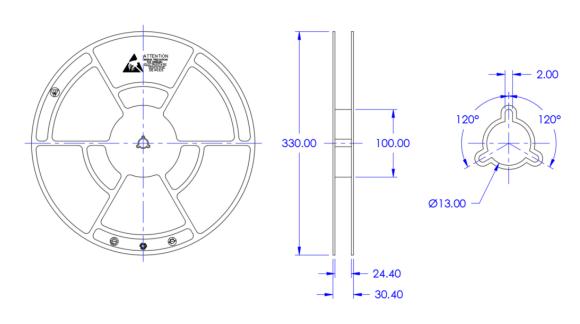


PACKING TYPE

Carrier Tape



<u>Reel</u>



All dimensions in millimeters Quantity per Reel: 2000 units



TOLL PACKAGE OUTLINE, PART MARKING, TAPE AND REEL SPECIFICATION	Page 4 of 4
DS_TOLL	Rev B

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REVISION HISTORY

Revision	Create Date (mm/dd/yyyy)	Description of Change	Initiator of Change
A	10/13/2023	Initial Production Release	Glenn Galang
В	01/31/2024	Corrected device orientation inside carrier tape pocket (Page 3)	Glenn Galang

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